

## AG FILM FOR POWER ELECTRONICS

### AG FILM CHARACTERISTICS

Ag sintering film	
Size (mm x mm)	100x100*
Thickness (µm) (±10%)	65
BLT** (µm) (±10%)	28
AG contents (wt.%)	> 98.0

- High adhesion at low sintering pressure: 250°C, MPa, 120sec
- Fast & easy film transfer (150°C, 2-3MPa, 0.5-3sec) / No burr issue
- Min. fume during sintering

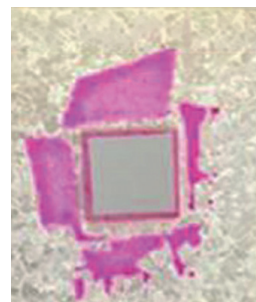
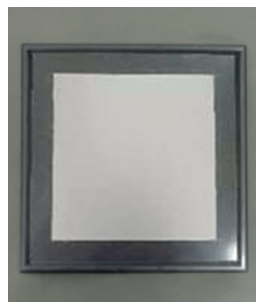
\*BLT: Bond Line Thickness after sintering



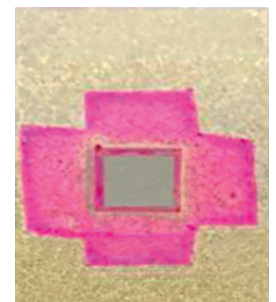
Roll



Sheet



Competitor's Film



AMO Film

## AG FILM TRANSFER

Test conditions

: PET release film (release force 8-13g/inch)

: Rubber hardness (shore A 50)

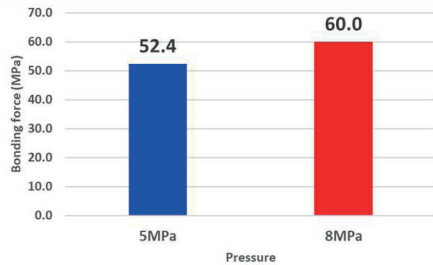
: Film transfer conditions

pressure - 2.0 MPa Temp - 150°C Time - 0.5sec



No burr after transfer

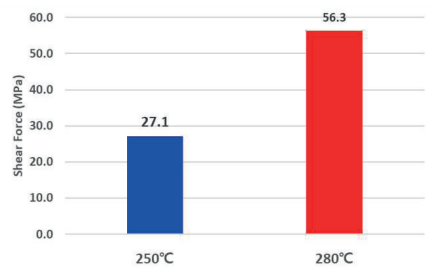
## SINTERING \_ AG DEPOSITED AMB SUBSTRATE



- ✓ Sintering temperature : 250°C
- ✓ Sintering time : 120 sec
- ✓ Chip surface finish : Au
- ✓ Chip size : 5\*5mm



## SINTERING \_ BARE AMB SUBSTRATE



- ✓ Sintering conditions : 250/280°C, 180sec, in Air
- ✓ Chip surface finish : Au
- ✓ Chip size : 5\*5mm

